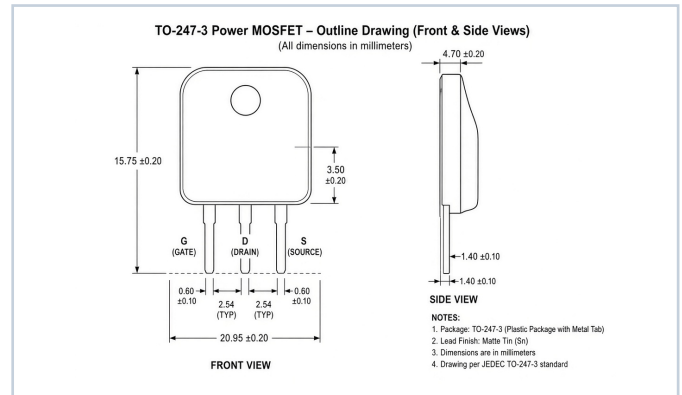
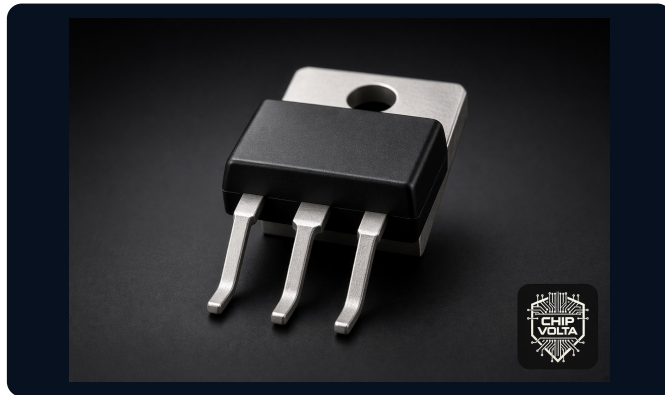


CV-SiC-1200-80

1200 V 80 mΩ SiC MOSFET · SiC MOSFETs

Package: TO-247-3



Description

Higher RDS(on) 1200 V SiC MOSFET for lower-power isolated converters where switching loss dominates conduction loss.

Features

- VDS 1200 V, RDS(on) typ 80 mΩ
- TO-247-3 industry footprint
- Tj max 175 °C
- Suitable for aux DC-DC and bias supplies

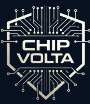
Typical applications

- Auxiliary DC-DC
- Isolated industrial supplies

Absolute maximum ratings

Parameter	Value	Unit
VDS	1200	V
VGS	–8 / +22	V
ID (Tc=25 °C)	22	A
Tj	–55 to +175	°C

Stresses beyond these limits may cause permanent damage. These are stress ratings only.



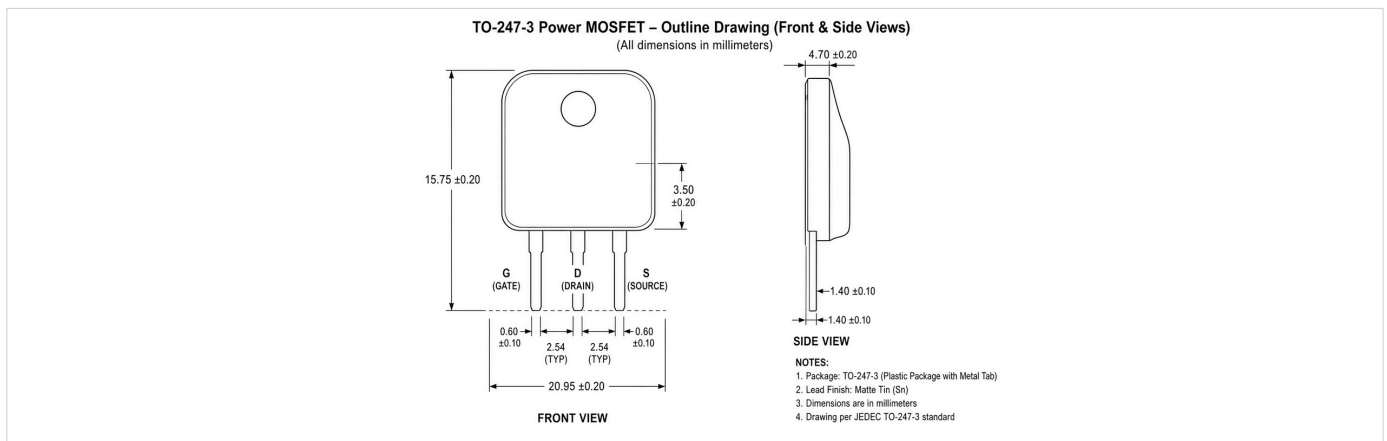
Electrical characteristics ($T_j = 25\text{ °C}$ unless noted)

Parameter	Min	Typ	Max	Unit
$V(BR)_{DSS}$	1200	—	—	V
$R_{DS(on)}$ 18 V, 25 °C	—	80	105	mΩ
$V_{GS(th)}$	1.8	2.7	4.2	V
Q_g	—	28	—	nC

Pin assignment (simplified)

Pin	Name	Function
1	G	Gate
2	D	Drain (tab)
3	S	Source

Package outline / mechanical sketch



Ordering and document control

This public brief supports schematic evaluation. The controlled datasheet (full electrical tables, SOA graphs, reliability summary, recommended land pattern and PPAP package) is released through Chip Volta applications engineering after an RFQ. Request it on the Contact / RFQ page quoting CV-SiC-1200-80. Samples follow the same path. Shorter lead-time builds use the released test program.

Quality: Chip Volta quality management system is certified by Bureau Veritas. Devices are specified to meet applicable industry standards. Values in this brief are typical catalog figures and may be revised without notice until the controlled revision is frozen for a customer program.